# 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD123W small and flat lead Surface-Mounted Device (SMD) plastic package.

### 2. Features and benefits

- Average forward current: I<sub>F(AV)</sub> ≤ 1 A
- Reverse voltage: V<sub>R</sub> ≤ 60 V
- Extremely low leakage current
- Low forward voltage
- High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified
- High temperature T<sub>i</sub> ≤ 175 °C

# 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; f = 20 kHz; $T_{sp} \le$ 170 °C; square wave	-	-	1	А
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 1 A; T <sub>j</sub> = 25 °C	-	605	660	mV
I <sub>R</sub>	reverse current	$V_R$ = 60 V; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C; pulsed	-	90	300	nA





# 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]	1 2	1 🔀 2
2	А	anode	SOD123W	sym001

<sup>[1]</sup> The marking bar indicates the cathode.

# 6. Ordering information

### Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG6010ELR	SOD123W	plastic surface mounted package; 2 leads	SOD123W			

# 7. Marking

## Table 4. Marking codes

Type number	Marking code
PMEG6010ELR	K1

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
I <sub>F</sub>	forward current	T <sub>sp</sub> = 165 °C; δ = 1		-	1.41	Α
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; f = 20 kHz; $T_{sp} \le$ 170 °C; square wave		-	1	A
		$\delta$ = 0.5; f = 20 kHz; $T_{amb} \le$ 140 °C; square wave	[1]	-	1	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	50	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	680	mW
			[3]	-	1150	mW
			[1]	-	2140	mW
T <sub>j</sub>	junction temperature			-	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1][2]	-	-	220	K/W
			[1][3]	-	-	130	K/W
			[1][4]	-	-	70	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	18	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of cathode tab.

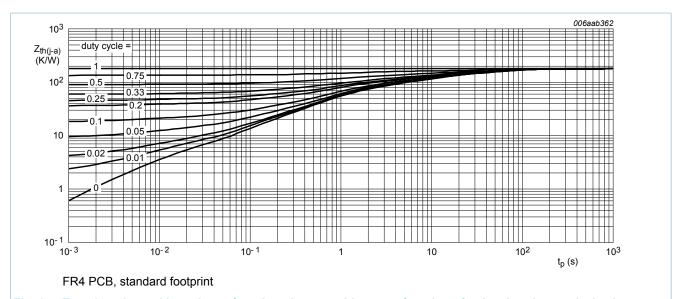


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

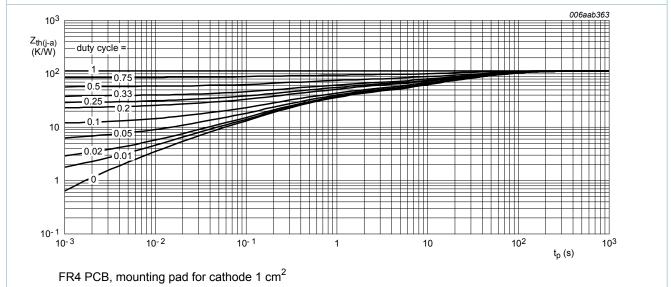
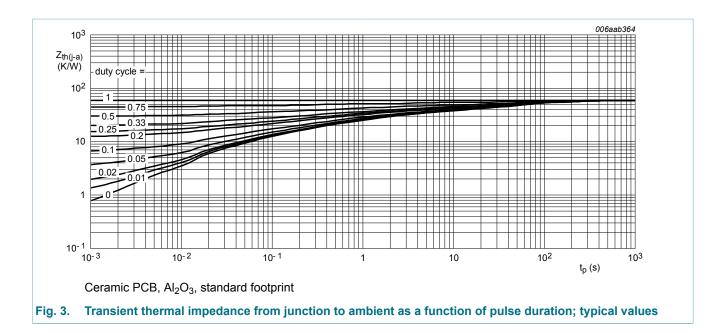


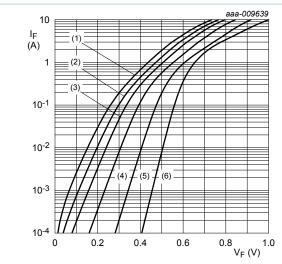
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



# 10. Characteristics

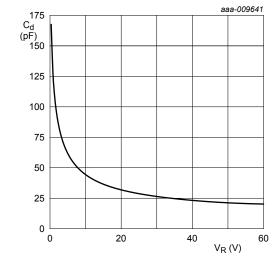
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage	I <sub>F</sub> = 0.1 A; T <sub>j</sub> = 25 °C	-	475	540	mV
		I <sub>F</sub> = 0.5 A; T <sub>j</sub> = 25 °C	-	550	605	mV
		I <sub>F</sub> = 0.7 A; T <sub>j</sub> = 25 °C	-	575	625	mV
		I <sub>F</sub> = 1 A; T <sub>j</sub> = 25 °C	-	605	660	mV
I <sub>R</sub>	reverse current	$V_R = 5 \text{ V}; t_p \le 300  \mu\text{s}; \delta \le 0.02;$ $T_j = 25 ^{\circ}\text{C}; \text{ pulsed}$	-	5	-	nA
		$V_R = 10 \text{ V; } t_p \le 300  \mu\text{s; } \delta \le 0.02;$ $T_j = 25 \text{ °C; pulsed}$	-	6	-	nA
		$V_R = 40 \text{ V; } t_p \le 300  \mu\text{s; } \delta \le 0.02;$ $T_j = 25 \text{ °C; pulsed}$	-	25	50	nA
		$V_R$ = 60 V; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_j$ = 25 °C; pulsed	-	90	300	nA
		$V_R$ = 10 V; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_j$ = 125 °C; pulsed	-	25	-	μA
		$V_R = 60 \text{ V; } t_p \le 300  \mu\text{s; } \delta \le 0.02;$ $T_j = 125 \text{ °C; pulsed}$	-	120	-	μA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	110	-	pF
		V <sub>R</sub> = 4 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	65	-	pF
		$V_R = 10 \text{ V; } f = 1 \text{ MHz; } T_j = 25 \text{ °C}$	-	45	-	pF
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	4.5	-	ns
V <sub>(BR)R</sub>	reverse breakdown voltage	I <sub>R</sub> = 1 mA; T <sub>j</sub> = 25 °C	60	-	-	V
$V_{FRM}$	peak forward recovery voltage	$I_F = 0.5 \text{ A}; \text{ d}I_F/\text{d}t = 20 \text{ A}/\mu\text{s}; T_j = 25 ^{\circ}\text{C}$	-	580	-	mV



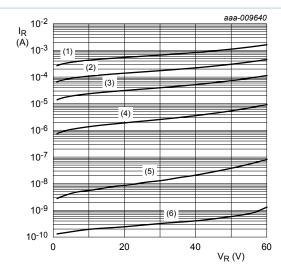
- (1)  $T_i = 175 \,^{\circ}C$
- (2)  $T_i = 150 \, ^{\circ}C$
- (3)  $T_i = 125 \, ^{\circ}C$
- (4)  $T_i = 85 \,^{\circ}C$
- (5)  $T_i = 25 \, ^{\circ}C$
- (6)  $T_i = -40 \, ^{\circ}C$

Fig. 4. Forward current as a function of forward voltage; typical values



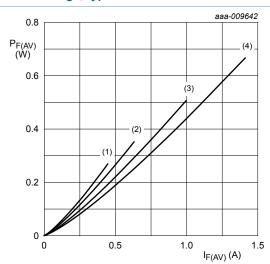
f = 1 MHz; T<sub>amb</sub> = 25 °C

Fig. 6. Diode capacitance as a function of reverse voltage; typical values



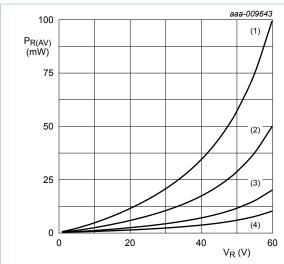
- (1)  $T_i = 175 \, ^{\circ}C$
- (2)  $T_i = 150 \, ^{\circ}\text{C}$
- (3)  $T_i = 125 \,^{\circ}C$
- (4)  $T_j = 85 \, ^{\circ}C$
- (5)  $T_i = 25 \, ^{\circ}C$
- (6)  $T_i = -40 \,^{\circ}\text{C}$

Fig. 5. Reverse current as a function of reverse voltage; typical values



- T<sub>i</sub> = 175 °C
- $(1) \delta = 0.1$
- $(2) \delta = 0.2$
- $(3) \delta = 0.5$
- $(4) \delta = 1$

ig. 7. Average forward power dissipation as a function of average forward current; typical values



T<sub>i</sub> = 150 °C

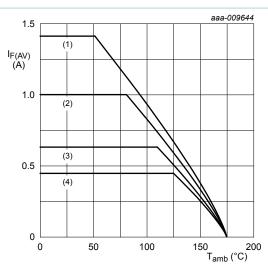
 $(1) \delta = 1$ 

 $(2) \delta = 0.5$ 

 $(3) \delta = 0.2$ 

 $(4) \delta = 0.1$ 

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T<sub>i</sub> = 175 °C

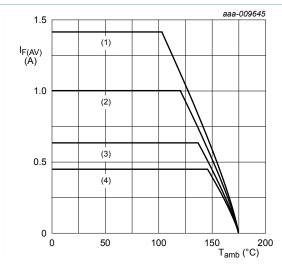
(1)  $\delta = 1$  (DC)

(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

 $T_j = 175$  °C

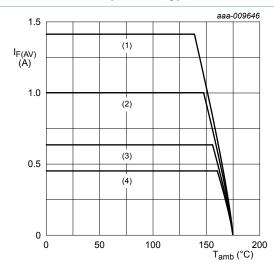
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

T<sub>i</sub> = 175 °C

(1)  $\delta = 1$  (DC)

(2)  $\delta$  = 0.5; f = 20 kHz

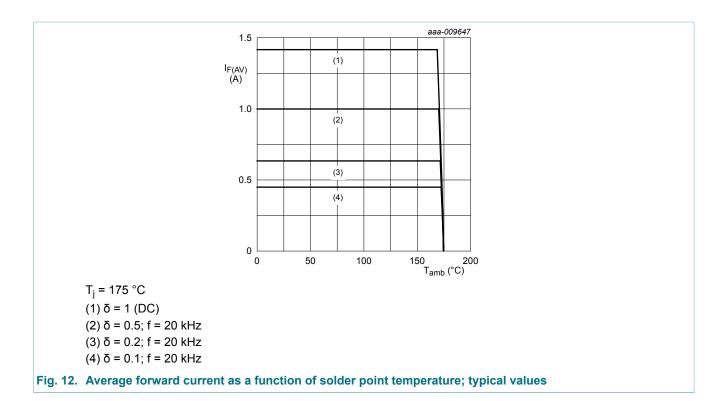
(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

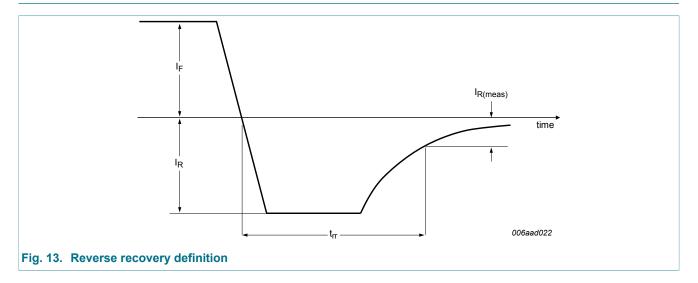
Fig. 11. Average forward current as a function of ambient temperature; typical values

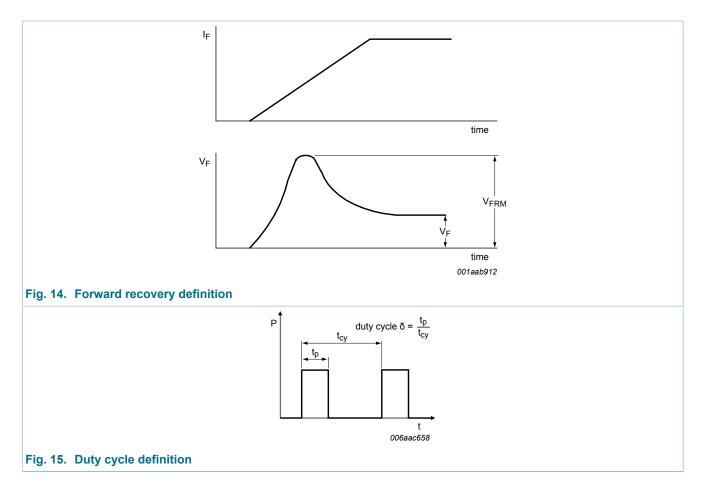
NXP Semiconductors PMEG6010ELR

60 V, 1 A low leakage current Schottky barrier rectifier



# 11. Test information





The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 12. Package outline

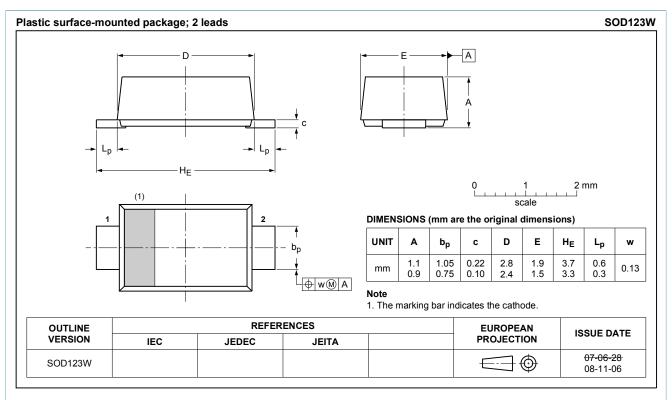
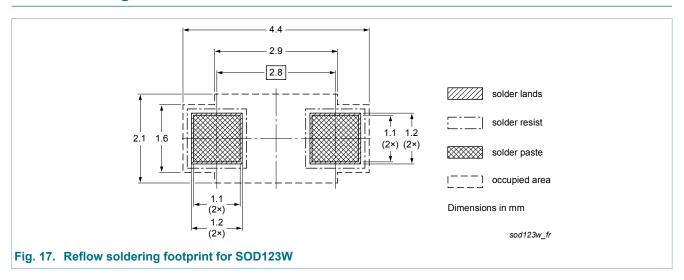


Fig. 16. Package outline SOD123W

# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6010ELR v.2	20140603	Product data sheet	-	PMEG6010ELR v.1
Modifications:	Product specification updated			
PMEG6010ELR v.1	20131108	Preliminary data sheet	-	-

# 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PMEG6010ELR

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NXP Semiconductors PMEG6010ELR

#### 60 V, 1 A low leakage current Schottky barrier rectifier

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